

# MJD2955 (PNP), MJD3055 (NPN)

## Complementary Power Transistors

### DPAK for Surface Mount Applications

Designed for general purpose amplifier and low speed switching applications.

#### Features

- Lead Formed for Surface Mount Applications in Plastic Sleeves (No Suffix)
- Straight Lead Version in Plastic Sleeves (“-1” Suffix)
- Electrically Similar to MJE2955 and MJE3055
- High Current Gain–Bandwidth Product
- Epoxy Meets UL 94 V-0 @ 0.125 in
- NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

#### MAXIMUM RATINGS

Rating	Symbol	Max	Unit
Collector–Emitter Voltage	$V_{CEO}$	60	Vdc
Collector–Base Voltage	$V_{CB}$	70	Vdc
Emitter–Base Voltage	$V_{EB}$	5	Vdc
Collector Current	$I_C$	10	Adc
Base Current	$I_B$	6	Adc
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D^\dagger$	20 0.16	W W/ $^\circ\text{C}$
Total Power Dissipation (Note 1) @ $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	1.75 0.014	W W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$
ESD – Human Body Model	HBM	3B	V
ESD – Machine Model	MM	C	V

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

†Safe Area Curves are indicated by Figure 1. Both limits are applicable and must be observed.

1. These ratings are applicable when surface mounted on the minimum pad sizes recommended.

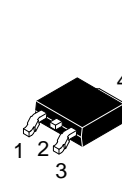
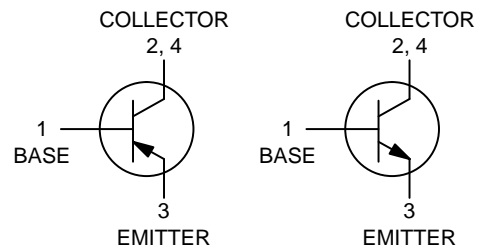


**ON Semiconductor®**

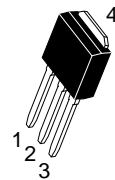
<http://onsemi.com>

### SILICON POWER TRANSISTORS 10 AMPERES 60 VOLTS, 20 WATTS

#### COMPLEMENTARY

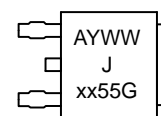


**DPAK  
CASE 369C  
STYLE 1**

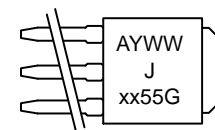


**IPAK  
CASE 369D  
STYLE 1**

#### MARKING DIAGRAMS



DPAK



IPAK

- A = Assembly Location
- Y = Year
- WW = Work Week
- Jxx55 = Device Code  
x = 29 or 30
- G = Pb-Free Package

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

# MJD2955 (PNP), MJD3055 (NPN)

## THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	6.25	$^{\circ}C/W$
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	71.4	$^{\circ}C/W$

2. These ratings are applicable when surface mounted on the minimum pad sizes recommended.

## ELECTRICAL CHARACTERISTICS ( $T_C = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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### OFF CHARACTERISTICS

Collector-Emitter Sustaining Voltage (Note 3) ( $I_C = 30 \text{ mAdc}$ , $I_B = 0$ )	$V_{CE(sus)}$	60	-	Vdc
Collector Cutoff Current ( $V_{CE} = 30 \text{ Vdc}$ , $I_B = 0$ )	$I_{CEO}$	-	50	$\mu\text{Adc}$
Collector Cutoff Current ( $V_{CE} = 70 \text{ Vdc}$ , $V_{EB(off)} = 1.5 \text{ Vdc}$ ) ( $V_{CE} = 70 \text{ Vdc}$ , $V_{EB(off)} = 1.5 \text{ Vdc}$ , $T_C = 150^{\circ}C$ )	$I_{CEX}$	-	$\frac{0.02}{2}$	mAdc
Collector Cutoff Current ( $V_{CB} = 70 \text{ Vdc}$ , $I_E = 0$ ) ( $V_{CB} = 70 \text{ Vdc}$ , $I_E = 0$ , $T_C = 150^{\circ}C$ )	$I_{CBO}$	-	$\frac{0.02}{2}$	mAdc
Emitter Cutoff Current ( $V_{BE} = 5 \text{ Vdc}$ , $I_C = 0$ )	$I_{EBO}$	-	0.5	mAdc

### ON CHARACTERISTICS

DC Current Gain (Note 3) ( $I_C = 4 \text{ Adc}$ , $V_{CE} = 4 \text{ Vdc}$ ) ( $I_C = 10 \text{ Adc}$ , $V_{CE} = 4 \text{ Vdc}$ )	$h_{FE}$	$\frac{20}{5}$	$\frac{100}{-}$	-
Collector-Emitter Saturation Voltage (Note 3) ( $I_C = 4 \text{ Adc}$ , $I_B = 0.4 \text{ Adc}$ ) ( $I_C = 10 \text{ Adc}$ , $I_B = 3.3 \text{ Adc}$ )	$V_{CE(sat)}$	-	$\frac{1.1}{8}$	Vdc
Base-Emitter On Voltage (Note 3) ( $I_C = 4 \text{ Adc}$ , $V_{CE} = 4 \text{ Vdc}$ )	$V_{BE(on)}$	-	1.8	Vdc

### DYNAMIC CHARACTERISTICS

Current-Gain - Bandwidth Product ( $I_C = 500 \text{ mAdc}$ , $V_{CE} = 10 \text{ Vdc}$ , $f = 500 \text{ kHz}$ )	$f_T$	2	-	MHz
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3. Pulse Test: Pulse Width  $\leq 300 \mu\text{s}$ , Duty Cycle  $\leq 2\%$ .

# MJD2955 (PNP), MJD3055 (NPN)

## TYPICAL CHARACTERISTICS

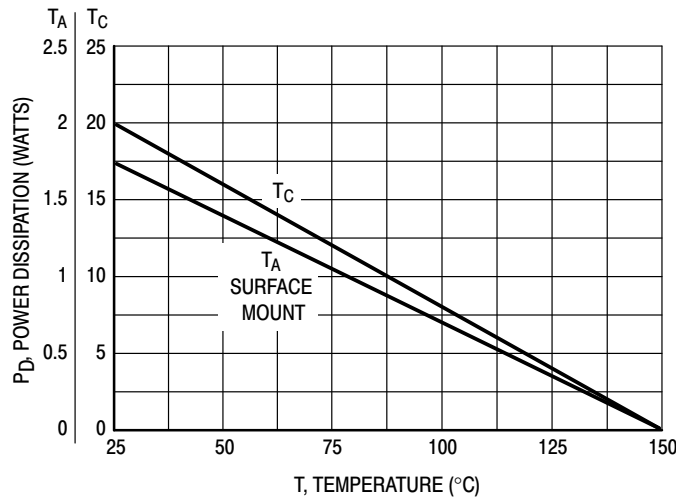


Figure 1. Power Derating

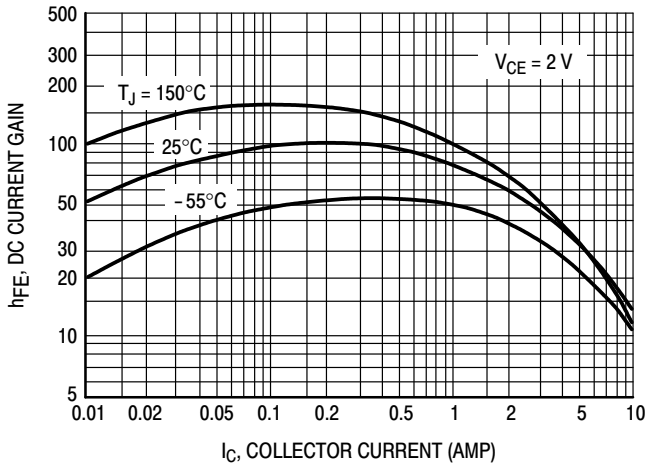


Figure 2. DC Current Gain

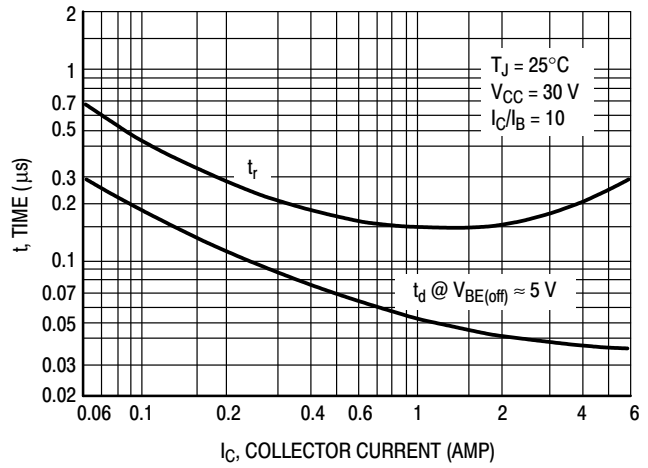


Figure 3. Turn-On Time

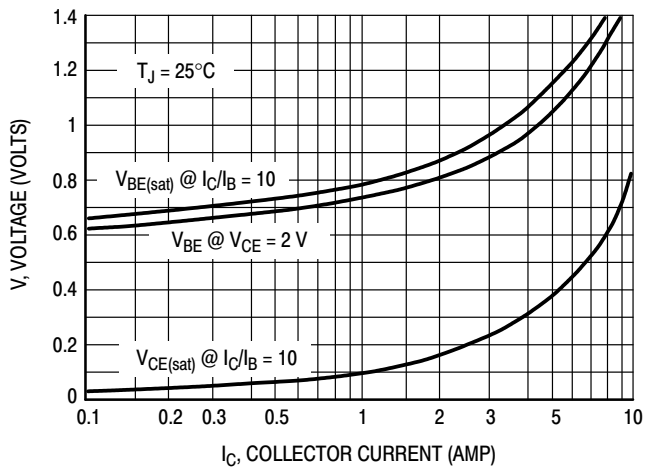


Figure 4. "On" Voltages, MJD3055

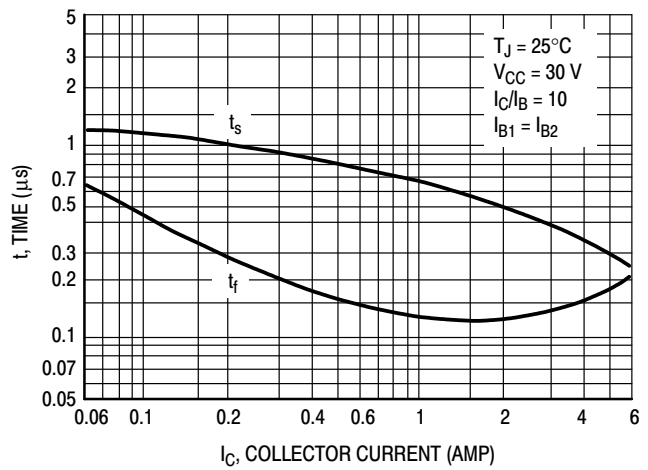


Figure 5. Turn-Off Time

## MJD2955 (PNP), MJD3055 (NPN)

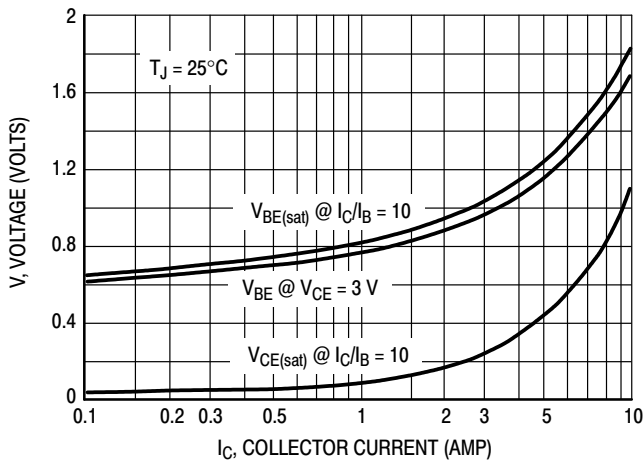


Figure 6. "On" Voltages, MJD2955

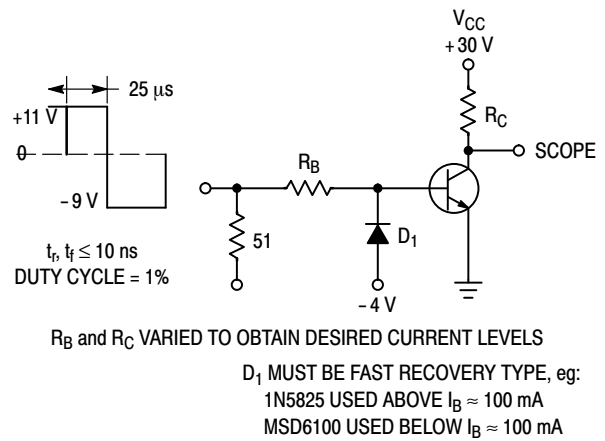


Figure 7. Switching Time Test Circuit

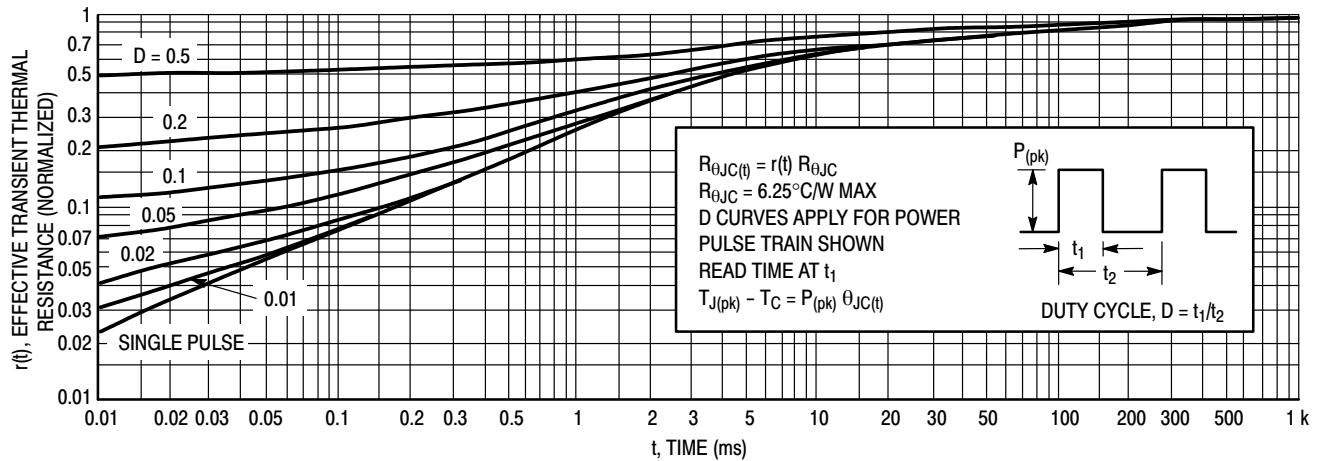


Figure 8. Thermal Response

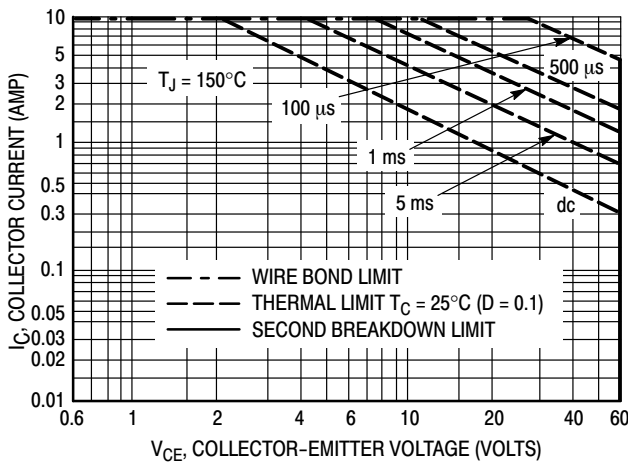


Figure 9. Maximum Forward Bias Safe Operating Area

### Forward Bias Safe Operating Area Information

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 9 is based on  $T_{J(pk)} = 150^\circ\text{C}$ ;  $T_C$  is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)} \leq 150^\circ\text{C}$ .  $T_{J(pk)}$  may be calculated from the data in Figure 8. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

## MJD2955 (PNP), MJD3055 (NPN)

### ORDERING INFORMATION

Device	Package Type	Package	Shipping <sup>†</sup>
MJD2955G	DPAK (Pb-Free)	369C	75 Units / Rail
MJD2955-1G	IPAK (Pb-Free)	369D	75 Units / Rail
MJD2955T4G	DPAK (Pb-Free)	369C	2,500 / Tape & Reel
NJVMJD2955T4G*	DPAK (Pb-Free)	369C	2,500 / Tape & Reel
MJD3055G	DPAK (Pb-Free)	369C	75 Units / Rail
MJD3055T4G	DPAK (Pb-Free)	369C	2,500 / Tape & Reel
NJVMJD3055T4G*	DPAK (Pb-Free)	369C	2,500 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

\*NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable

# MECHANICAL CASE OUTLINE

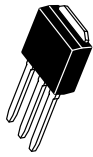
## PACKAGE DIMENSIONS

ON Semiconductor®

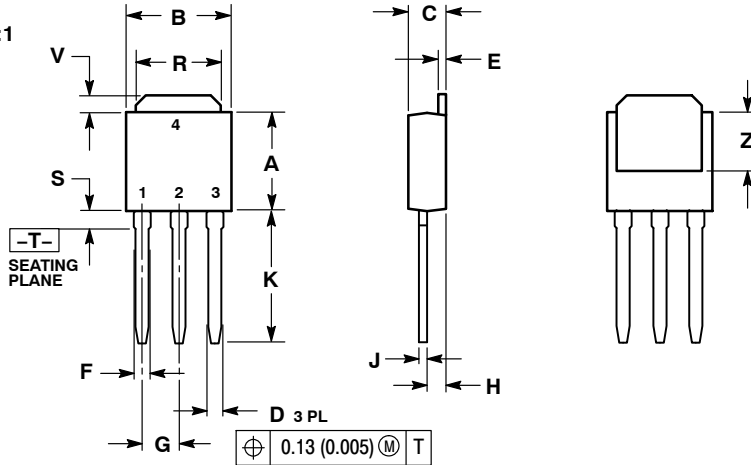


### IPAK CASE 369D-01 ISSUE C

DATE 15 DEC 2010



SCALE 1:1

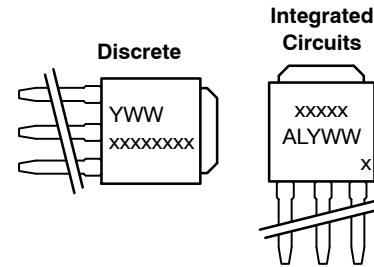


- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.235	0.245	5.97	6.35
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.090	BSC	2.29	BSC
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.350	0.380	8.89	9.65
R	0.180	0.215	4.45	5.45
S	0.025	0.040	0.63	1.01
V	0.035	0.050	0.89	1.27
Z	0.155	---	3.93	---

- |  |   |  |  |
|--|---|--|--|
| <p>STYLE 1:<br/>PIN 1. BASE<br/>2. COLLECTOR<br/>3. EMITTER<br/>4. COLLECTOR</p> | <p>STYLE 2:<br/>PIN 1. GATE<br/>2. DRAIN<br/>3. SOURCE<br/>4. DRAIN</p> | <p>STYLE 3:<br/>PIN 1. ANODE<br/>2. CATHODE<br/>3. ANODE<br/>4. CATHODE</p>      | <p>STYLE 4:<br/>PIN 1. CATHODE<br/>2. ANODE<br/>3. GATE<br/>4. ANODE</p> |
| <p>STYLE 5:<br/>PIN 1. GATE<br/>2. ANODE<br/>3. CATHODE<br/>4. ANODE</p>         | <p>STYLE 6:<br/>PIN 1. MT1<br/>2. MT2<br/>3. GATE<br/>4. MT2</p>        | <p>STYLE 7:<br/>PIN 1. GATE<br/>2. COLLECTOR<br/>3. EMITTER<br/>4. COLLECTOR</p> |  |

### MARKING DIAGRAMS

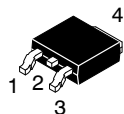


- xxxxxxxx = Device Code  
A = Assembly Location  
IL = Wafer Lot  
Y = Year  
WW = Work Week

DOCUMENT NUMBER:	98AON10528D	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	IPAK (DPAK INSERTION MOUNT)	PAGE 1 OF 1

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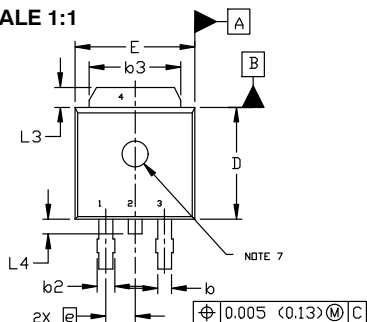
# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



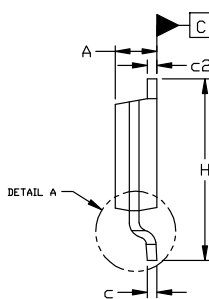
## DPAK (SINGLE GAUGE) CASE 369C ISSUE G

DATE 31 MAY 2023

SCALE 1:1



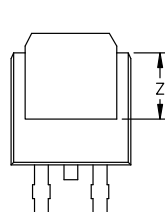
TOP VIEW



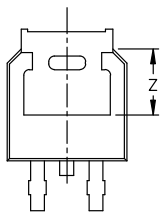
SIDE VIEW

NOTES:

1. DIMENSIONING AND TOLERANCING ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3, AND Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.
7. OPTIONAL MOLD FEATURE.

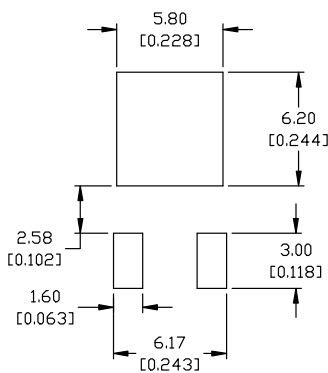


BOTTOM VIEW



BOTTOM VIEW

ALTERNATE CONSTRUCTIONS



RECOMMENDED MOUNTING FOOTPRINT\*

\*FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERM/D.

STYLE 1:

- PIN 1. BASE
- 2. COLLECTOR
- 3. EMITTER
- 4. COLLECTOR

STYLE 2:

- PIN 1. GATE
- 2. DRAIN
- 3. SOURCE
- 4. DRAIN

STYLE 3:

- PIN 1. ANODE
- 2. CATHODE
- 3. ANODE
- 4. CATHODE

STYLE 4:

- PIN 1. CATHODE
- 2. ANODE
- 3. GATE
- 4. ANODE

STYLE 5:

- PIN 1. GATE
- 2. ANODE
- 3. CATHODE
- 4. ANODE

STYLE 6:

- PIN 1. MT1
- 2. MT2
- 3. GATE
- 4. MT2

STYLE 7:

- PIN 1. GATE
- 2. COLLECTOR
- 3. EMITTER
- 4. COLLECTOR

STYLE 8:

- PIN 1. N/C
- 2. CATHODE
- 3. ANODE
- 4. CATHODE

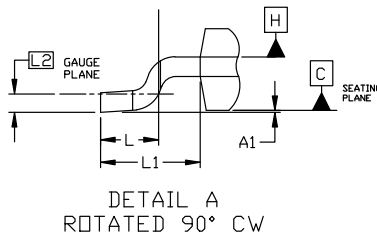
STYLE 9:

- PIN 1. ANODE
- 2. CATHODE
- 3. RESISTOR ADJUST
- 4. CATHODE

STYLE 10:

- PIN 1. CATHODE
- 2. ANODE
- 3. CATHODE
- 4. ANODE

DIM	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
A	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.028	0.045	0.72	1.14
b3	0.180	0.215	4.57	5.46
c	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
e	0.090	BSC	2.29	BSC
H	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.114	REF	2.90	REF
L2	0.020	BSC	0.51	BSC
L3	0.035	0.050	0.89	1.27
L4	----	0.040	---	1.01
Z	0.155	----	3.93	---

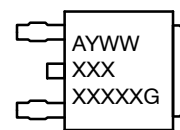


DETAIL A  
ROTATED 90° CW

### GENERIC MARKING DIAGRAM\*



IC



Discrete

- XXXXXX = Device Code
- A = Assembly Location
- L = Wafer Lot
- Y = Year
- WW = Work Week
- G = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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<b>DESCRIPTION:</b>	<b>DPAK (SINGLE GAUGE)</b>	<b>PAGE 1 OF 1</b>

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